

METHOD OF PROCESSING WAFER

ABSTRACT

A method of processing a wafer includes a first processed groove forming step of applying a laser beam to the wafer from a face side thereof along projected dicing lines to form first processed grooves, after the first processed groove forming step, a masking protective film forming step of forming a masking protective film covering the face side of the wafer and filling the first processed grooves, after the masking protective film forming step, a second processed groove forming step of applying a laser beam to the wafer along the first processed grooves to form second processed grooves that are narrower than the first processed grooves, exposing the substrate through the second processed grooves, and after the second processed groove forming step, a plasma etching step of carrying out plasma etching on the wafer along the second processed grooves using the masking protective film as a mask.

[FIG. 3]